

ULTRAFast RECTIFIER PDP ENERGY RECOVERY

Table 1: Main Product Characteristics

$I_{F(AV)}$	40 A
V_{RRM}	300 V
$V_{FP} (typ)$	2.5 V
$I_{RM} (typ)$	5 A
T_j	175°C
$V_F (typ)$	0.9 V

FEATURES AND BENEFITS

- Ultrafast recovery allowing High Sustain Frequency
- Decrease charge evacuation time (t_{clamp}) in the inductance (see figures 1 and 2)
- Minimize switching-on and total power losses
- Increase luminous efficiency and brightness
- Soft and noise-free recovery
- High surge capability
- High junction temperature

DESCRIPTION

The **STTH40P03S** is an Ultrafast Recovery Power Rectifier dedicated to **energy recovery in PDP application**.

The key parameters of the D_{ERC} diode for the energy recovery circuit have been optimized in order to decrease power losses.

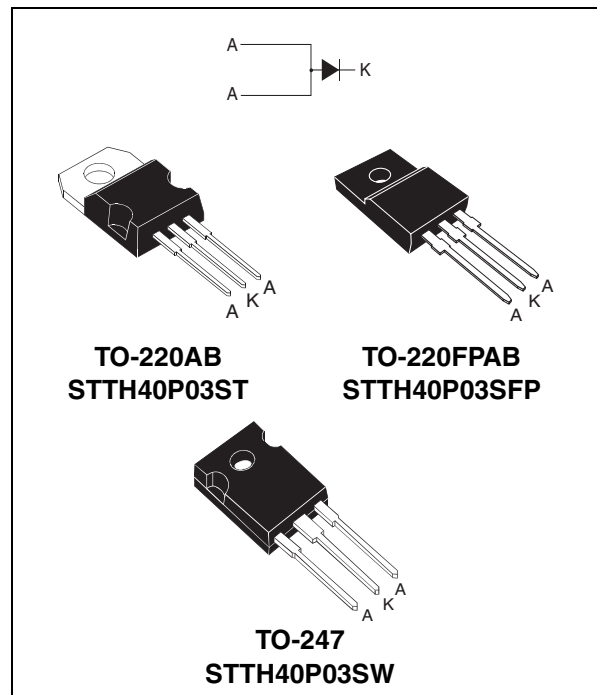


Table 2: Order Codes

Part Number	Marking
STTH40P03ST	STTH40P03S
STTH40P03SFP	STTH40P03S
STTH40P03SW	STTH40P03S

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		300	V
$I_{F(RMS)}$	RMS forward current		80	A
$I_{F(AV)}$	Average forward current		40	A
I_{FRM}	Repetitive peak forward current	$F = 200kHz, t_p = 500ns$ Sinusoidal waveform	120	A
T_{stg}	Storage temperature range		-65 to + 175	°C
T_j	Maximum operating junction temperature		175	°C

Table 4: Thermal Parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / TO-247	1.15	°C/W
		TO-220FPAB	4.5	
$Z_{th(j-c)}$	Transient thermal resistance at 1μs		0.002	°C/W

Table 5: Static Electrical Characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			50	μA
		$T_j = 125^\circ\text{C}$			0.05	0.5	mA
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 20\text{A}$			1.5	V
		$T_j = 125^\circ\text{C}$			0.9	1.15	
		$T_j = 25^\circ\text{C}$	$I_F = 40\text{A}$		1.1	1.8	V
		$T_j = 125^\circ\text{C}$				1.42	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$ ** $t_p = 380\text{ μs}$, $\delta < 2\%$ To evaluate the conduction losses use the following equation: $P = 0.88 \times I_{F(AV)} + 0.0135 I_F^2(RMS)$

Table 6: Switching Characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_{RM}	Reverse recovery current	$T_j = 100^\circ\text{C}$	$I_F = 40\text{A}$ $V_R = 100\text{V}$ $di_F/dt = 200\text{ A/μs}$		5	6.5	A
S_{factor}	Softness factor				0.5		-

Figure 1: Application Characteristics

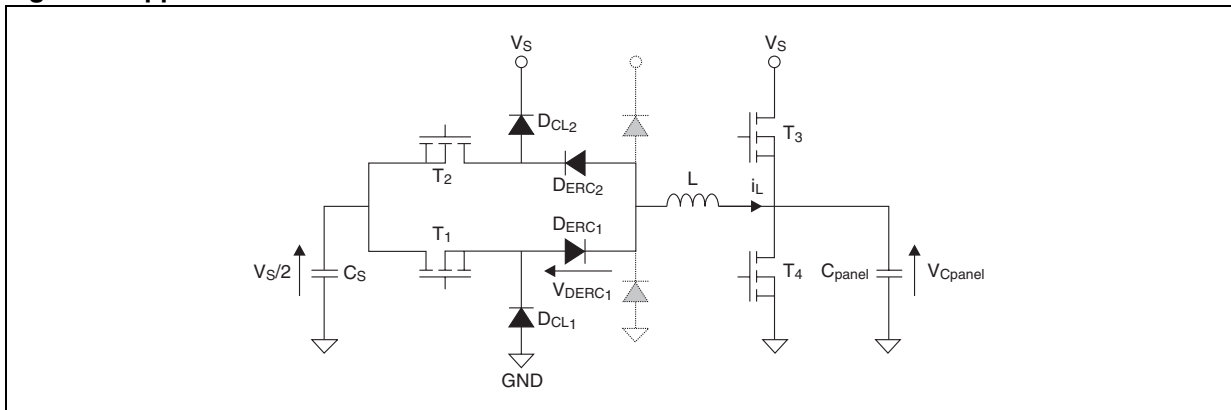


Figure 2: Application Waveforms

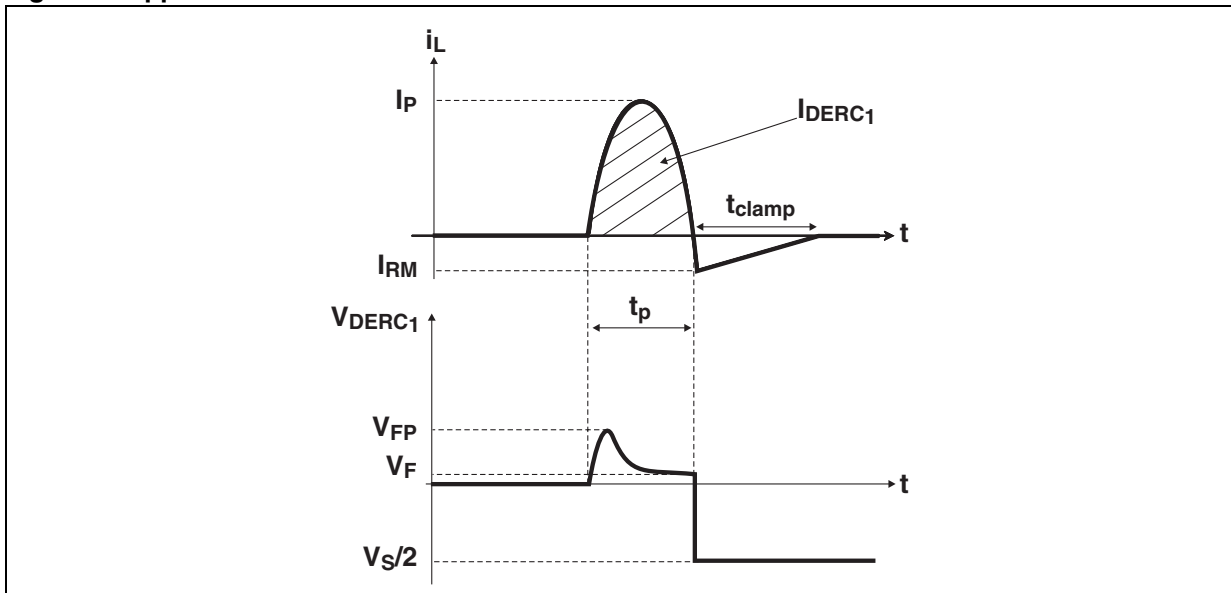


Figure 3: Forward voltage drop versus forward current

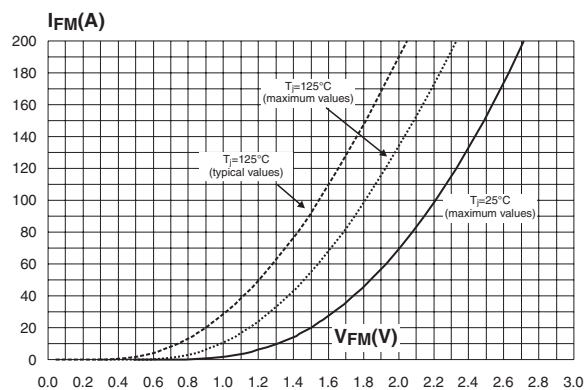


Figure 4: Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB / TO-247)

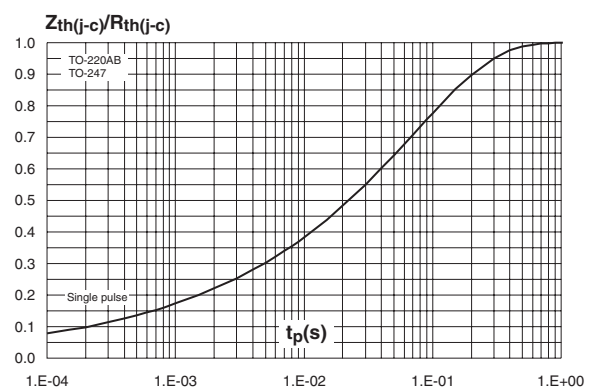


Figure 5: Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB)

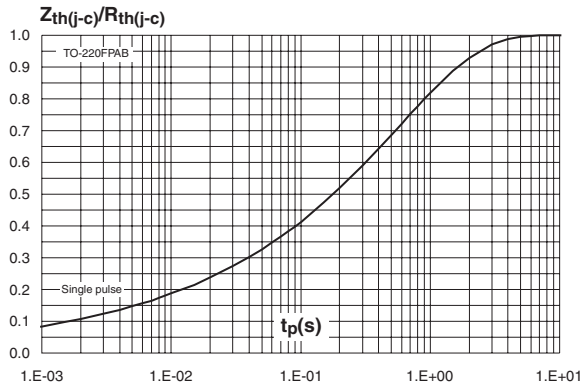


Figure 6: Peak reverse recovery current versus di_F/dt (typical values)

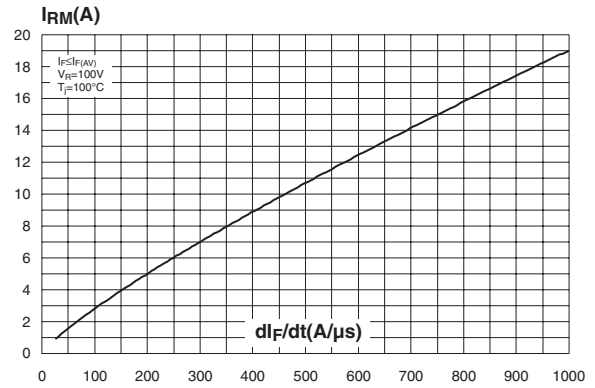


Figure 7: Reverse recovery time versus di_F/dt (typical values)

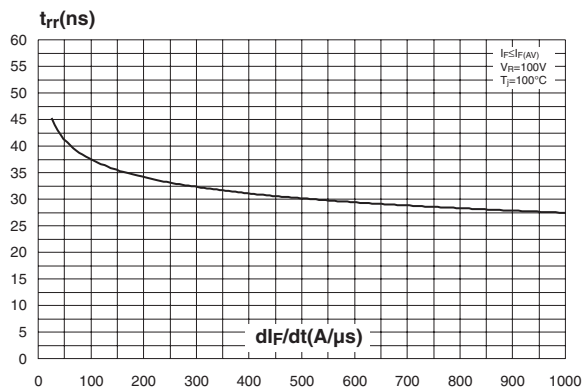


Figure 8: Reverse recovery softness factor versus di_F/dt (typical values)

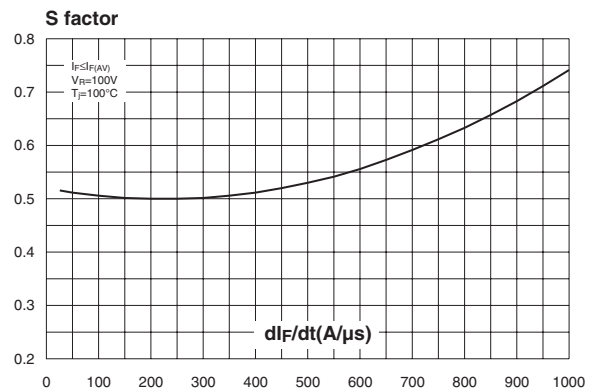


Figure 9: Relative variations of dynamic parameters versus junction temperature

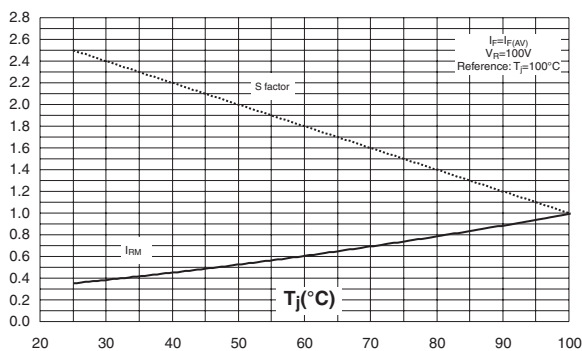


Figure 10: Transient peak forward voltage versus di_F/dt (typical values)

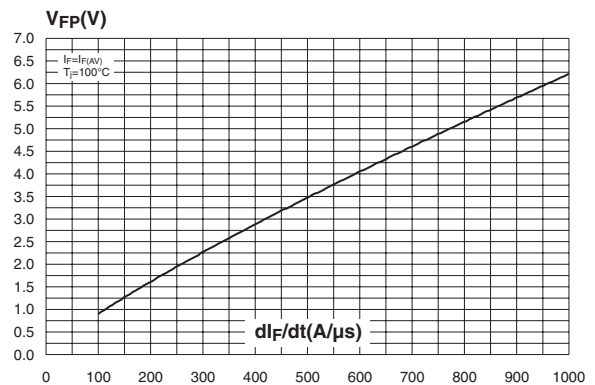


Figure 11: Forward recovery time versus di_F/dt (typical values)

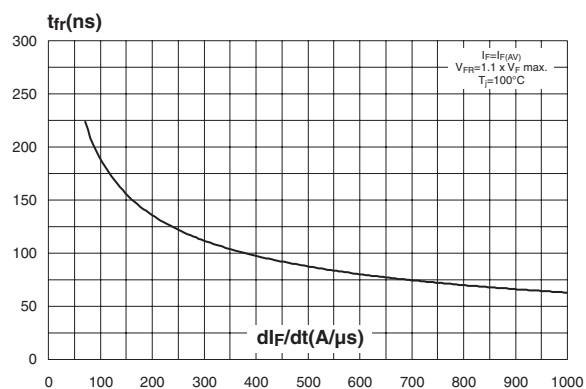


Figure 12: TO-220FPAB Package Mechanical Data

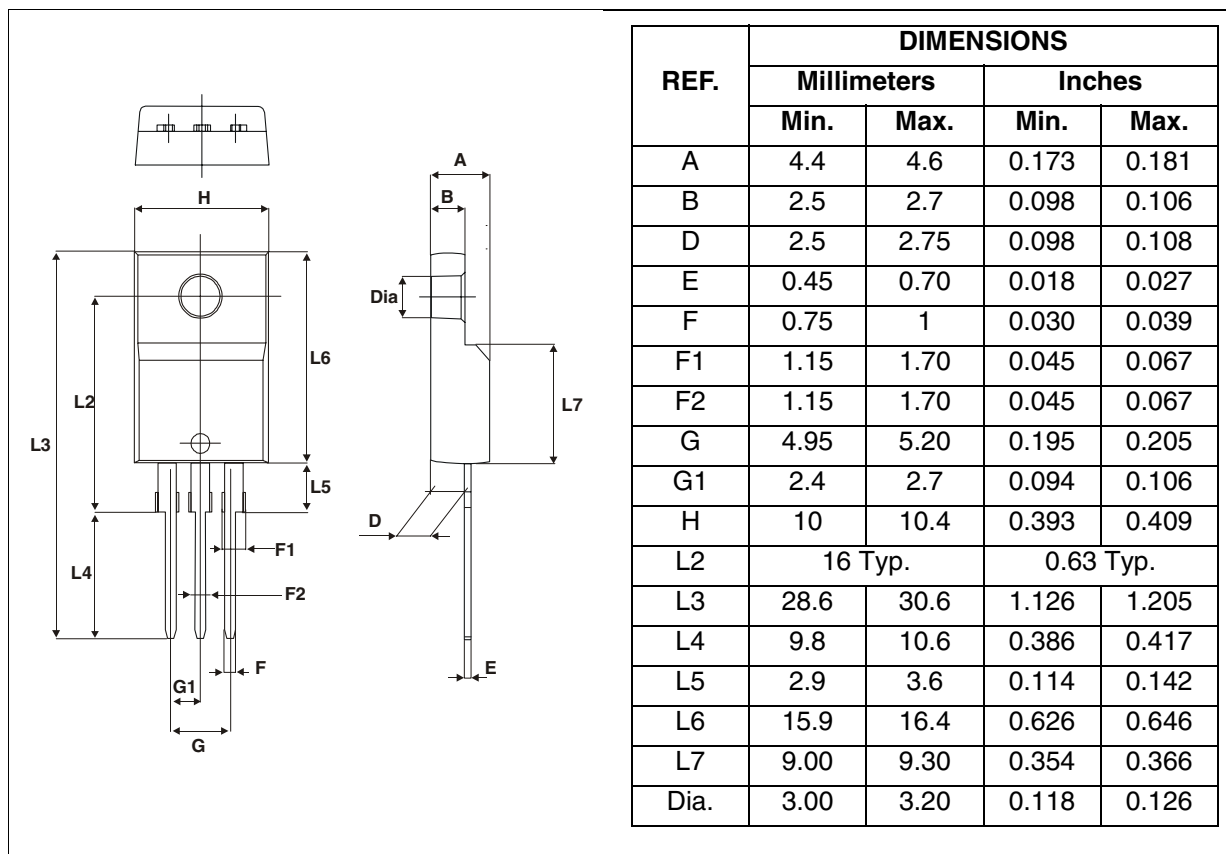


Figure 13: TO-247 Package Mechanical Data

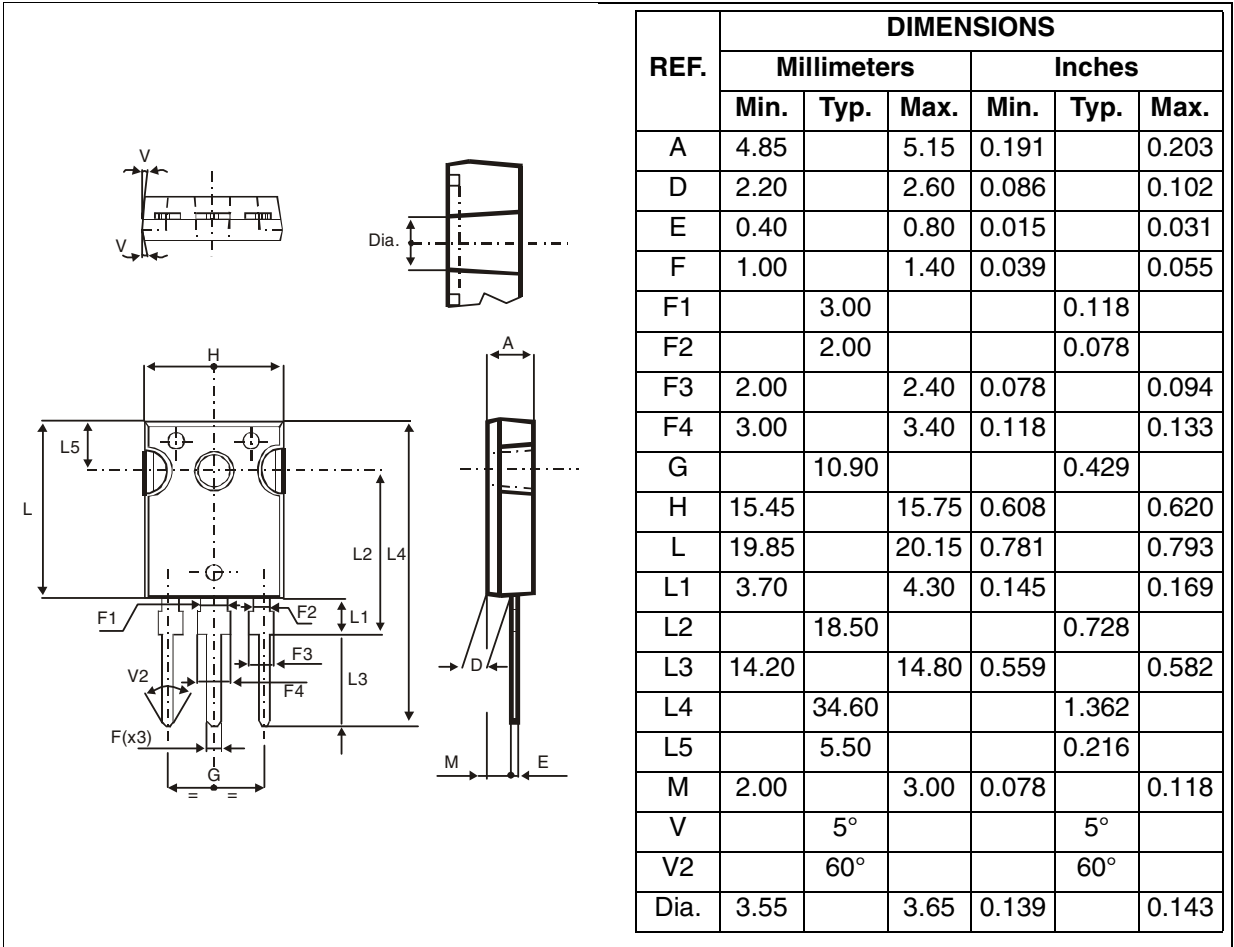


Figure 14: TO-220AB Package Mechanical Data

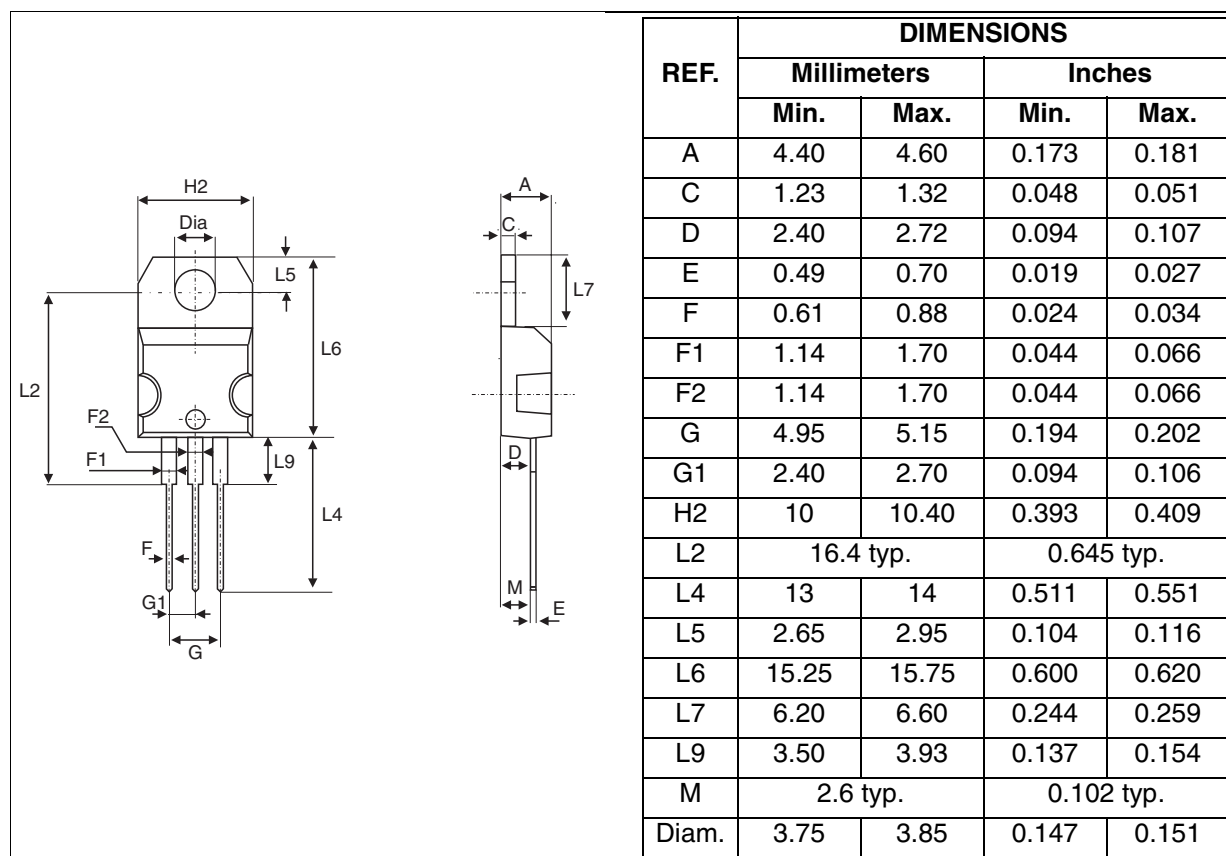


Table 7: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH40P03ST	STTH40P03S	TO-220AB	2.23 g	50	Tube
STTH40P03SFP	STTH40P03S	TO-220FPAB	2.0 g	50	Tube
STTH40P03SW	STTH40P03S	TO-247	4.36 g	30	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 m.N.
- Maximum torque value: 0.70 m.N.

Table 8: Revision History

Date	Revision	Description of Changes
06-Jul-2005	1	First issue.

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com